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Declarations under Rule 4.17:

— as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))

[Continued on next page]

(54) Title: METHOD FOR LOW-K DIELECTRIC ETCH WITH REDUCED DAMAGE

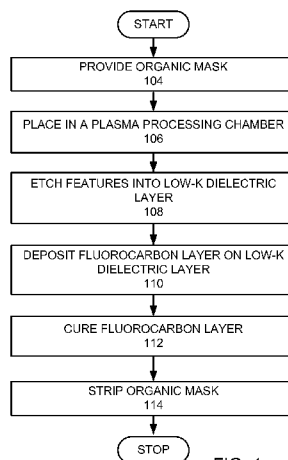


FIG. 1

(57) Abstract: A method for etching features in a low-k dielectric layer disposed below an organic mask is provided by an embodiment of the invention. Features are etched into the low-k dielectric layer through the organic mask. A fluorocarbon layer is deposited on the low-k dielectric layer. The fluorocarbon layer is cured. The organic mask is stripped.



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